AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. **(currently amended)** A method of passivating a semiconductor device, said method comprising:

placing a semiconductor device in a chamber, the semiconductor device having a first type of transistors and a second type of transistors;

introducing a first passivating gas and a second passivating gas into the chamber, wherein the first passivating gas and the second passivating gas are adapted to passivate the first type of transistors and the second type of transistors, respectively; and

heating the semiconductor device to a temperature for a period sufficient to passivate the semiconductor device.

2. **(canceled)**

3. (original) The method as claimed in claim 1, wherein the first passivating gas is H_2 or N_2.

4. (original) The method as claimed in claim 3, wherein the second passivating gas is H_2O or NH_3.

5. (original) The method as claimed in claim 1, wherein the first type of transistors are PMOS transistors and the second type of transistors are NMOS transistors.

6. (original) The method as claimed in claim 1, wherein the first and the second passivating gases are introduced into the chamber simultaneously.

7. (original) The method as claimed in claim 1, wherein the first passivating gas is introduced into the chamber and the semiconductor device is heated to a temperature for a period sufficient to passivate the first type of transistors, and then the second passivating gas is introduced into the chamber and the semiconductor device is heated to a temperature for a period sufficient to passivate the second type of transistors.

8. **(currently amended)** A method of passivating a semiconductor device, said method comprising:

placing a semiconductor device in a chamber, the semiconductor device having a first type of transistors and a second type of transistors;

introducing a first passivating gas and a second passivating gas into the chamber; and

heating the semiconductor device to a temperature for a period sufficient to passivate the semiconductor device;

wherein

the first passivating gas is introduced into the chamber and the semiconductor device is heated to a temperature for a period sufficient to passivate the first type of transistors, and then the second passivating gas is introduced into the chamber and the semiconductor device is heated to a temperature for a period sufficient to passivate the second type of transistors; and

~~The method as claimed in claim 7, wherein~~ the first passivating gas is drained out of the chamber by introducing the second passivating gas into the chamber and the pressure of the chamber is greater than 1 atmosphere.

9. (original) The method as claimed in claim 1, wherein the semiconductor

device comprises a CMOS circuit of an active matrix display device.

10. (original) The method as claimed in claim 1, wherein the chamber maintains a pressure between 5 atmospheres and 20 atmospheres.

11. (original) The method as claimed in claim 1, wherein the first type of transistors are PMOS transistors and the first passivating gas is H_2 or N_2, and the second type of transistors are NMOS transistors and the second passivating gas is H_2O or NH_3.

12. **(new)** The method as claimed in claim 7, wherein the first passivating gas is drained out of the chamber by introducing the second passivating gas into the chamber and the pressure of the chamber is greater than 1 atmosphere.

13. **(new)** The method as claimed in claim 1, wherein the first passivating gas is H_2.

14. **(new)** The method as claimed in claim 1, wherein the second passivating gas is H_2O.

15. **(new)** The method as claimed in claim 1, wherein the first and the second passivating gases are different gases which are introduced into the chamber simultaneously.

16. **(new)** The method as claimed in claim 1, wherein the first type of transistors are PMOS transistors and the first passivating gas is H_2, and the second type of transistors are NMOS transistors and the second passivating gas is H_2O.

17. **(new)** A method of passivating a semiconductor device, said method comprising:

providing the semiconductor device having first transistors of a first type and second transistors of a second type different from the first type;

placing the semiconductor device in a chamber; and

passivating the first and second transistors with first and second passivating gases, respectively;

wherein said passivating comprises

introducing the first and second passivating gases into the chamber; and

heating the semiconductor device to a predetermined temperature for a predetermined period sufficient for the first and second passivating gases to passivate the first and second transistors, respectively.

18. **(new)** The method as claimed in claim 17, wherein the first and second passivating gases are different gases.

19. **(new)** The method as claimed in claim 18, wherein the first and second passivating gases are introduced into the chamber simultaneously.

20. **(new)** The method as claimed in claim 17, wherein the first transistors are PMOS transistors, the second transistors are NMOS transistors, the first passivating gas is H_2 or N_2, and the second passivating gas is H_2O or NH_3.

21. **(new)** The method as claimed in claim 17, wherein the first transistors are PMOS transistors and the first passivating gas is H_2, whereas the second transistors are NMOS transistors and the second passivating gas is H_2O.